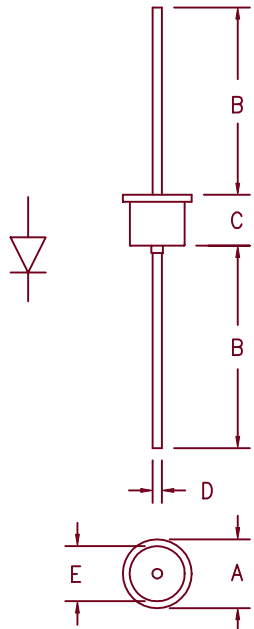
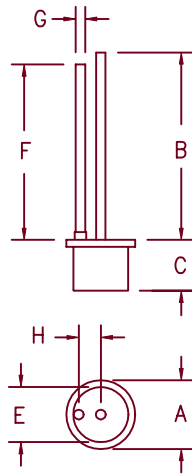


Silicon Rectifiers

1N4719–1N4725, 1N4997–1N5003



1N4719–1N4725



1N4997–1N5003

Dim.	Inches		Millimeter		Notes
	Minimum	Maximum	Minimum	Maximum	
A	---	.450	---	11.43	Dia.
B	.980	---	24.89	---	
C	---	.300	---	7.62	
D	.046	.056	1.17	1.42	Dia.
E	---	.350	---	8.89	Dia.
F	.960	---	24.38	---	
G	.031	.035	.79	.89	Dia.
H	.145	.165	3.68	4.19	

Microsemi Catalog Number	Peak Reverse Voltage
1N4719, 1N4997	50V
1N4720, 1N4998	100V
1N4721, 1N4999	200V
1N4722, 1N5000	400V
1N4723, 1N5001	600V
1N4724, 1N5002	800V
1N4725, 1N5003	1000V

- High Surge Capability
- 175°C Junction Temperature
- VRRM 50 to 1000 Volts
- 3 Amp Current Rating
- Hermetically Sealed

Electrical Characteristics		
Average forward current	I _{F(AV)} 3.0 Amps	T _A = 119°C, Square wave, R _{θJL} = 12°C/W, L = 1/4"
Maximum surge current	I _{FSM} 300 Amps	8.3ms, half sine, T _J = 175°C
Max peak forward voltage	V _{FM} 1.0 Volts	I _{FM} = 3.0A: T _J = 25°C*
Max peak reverse current	I _{RM} 25 μA	V _R = 25V, T _J = 25°C

*Pulse test: Pulse width 300 μsec, Duty cycle 2%

Thermal and Mechanical Characteristics		
Storage temperature range	T _{STG}	-65°C to 175°C
Operating junction temp range	T _J	-65°C to 175°C
Maximum thermal resistance	L = 1/4" R _{θJL}	12°C/W Junction to Lead
Weight		.08 ounces (2.3 grams) typical

12-11-01 Rev. 2

1N4719–1N4725, 1N4997–1N5003

Figure 1
Typical Forward Characteristics

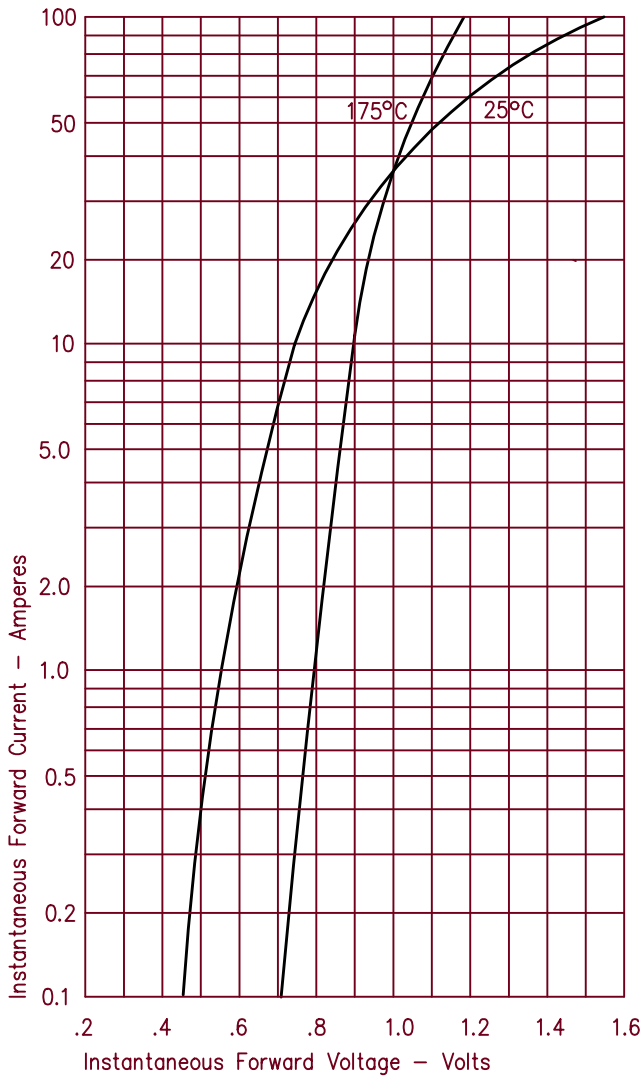


Figure 3
Forward Current Derating

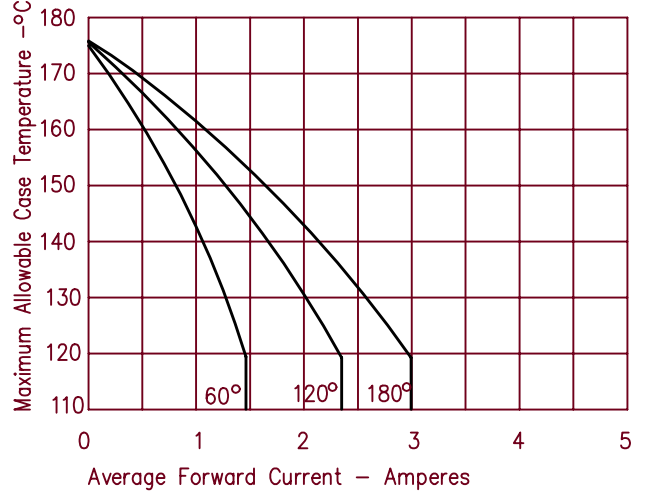


Figure 2
Typical Reverse Characteristics

